Hex 3-State Noninverting Buffer with Separate 2-Bit and 4-Bit Sections

High-Performance Silicon-Gate CMOS

The MC74HC367A is identical in pinout to the LS367. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

This device is arranged into 2-bit and 4-bit sections, each having its own active-low Output Enable. When either of the enables is high, the affected buffer outputs are placed into high-impedance states. The HC367A has noninverting outputs.

Features

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- These are Pb-Free Devices

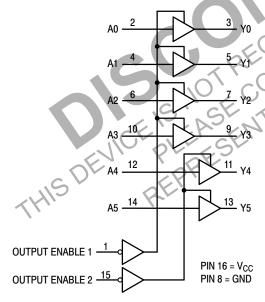
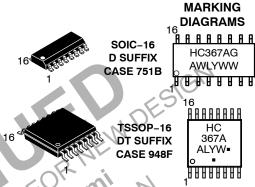


Figure 1. Logic Diagram



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A = Assembly Location

VL, L = Wafer Lot YY, Y = Year

WW, W = Work Week
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT

OUTPUT ENABLE 1	1 •	16	V _{CC}
A0 [Y0 [3	15 14	OUTPUT ENABLE 2 A5
A1 [4	13] Y5
Y1 [5	12] A4
A2 [6	11] Y4
Y2 [7	10] A3
GND [8	9] Y3

FUNCTION TABLE

Inpu	Output	
Enable 1, Enable 2	Α	Υ
L	L	L
L	Н	Н
Н	X	Z

X = don't care Z = high impedance

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	±20	mA
I _{out}	DC Output Current, per Pin	±25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	±50	mA
P _D	Power Dissipation in Still Air, SOIC Package TSSOP Package	500 450	mW
T _{stg}	Storage Temperature	-65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

T _{stg}					`. •	
	Storage Temperature	-65 to +	150	°C	Unused outputs must be	e left o
ings only tended e iability.	xceeding Maximum Ratings may damage the device. May, Functional operation above the Recommended Operation exposure to stresses above the Recommended Operating	ng Condition	ons is no	t implied.	NEW DESIGN	1
ymbol	Parameter	Min	Max	Unit	N	
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	NE	
' _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND) 0	V _{CC}	V	2	
T _A	Operating Temperature, All Package Types	-55	+125	°C	en ON	
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0$ (Figure 2) $V_{CC} = 3.0$ $V_{CC} = 4.5$ $V_{CC} = 6.0$	V 0	1000 600 500 400	ns	RNATION	
	Voc = 4.5 Voc = 6.0 Voc =	NE	.O.			

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

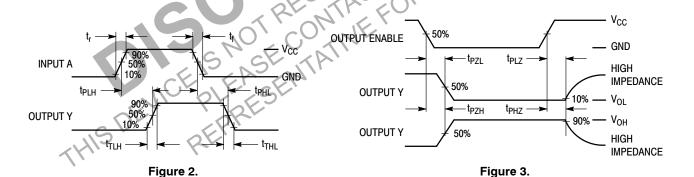
				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V _{CC} V	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\label{eq:Vin} \begin{array}{ll} V_{in} = V_{IH} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{array}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\begin{aligned} V_{in} = V_{IL} & I_{out} \leq 3.6 \text{ mA} \\ I_{out} \leq 6.0 \text{ mA} \\ I_{out} \leq 7.8 \text{ mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	±0.1	± 1.0	± 1.0	μΑ
l _{OZ}	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or V_{IH} $V_{out} = V_{CC}$ or GND	6.0	±0.5	± 5.0	± 10	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 μA	6.0	4	40	160	μΑ
ζ'	Maximum Quiescent Supply Current (per Package)	OT RONTHE FOR					

AC ELECTRICAL CHARACTERISTICS (C_L = 50 pF, Input t_r = t_f = 6 ns)

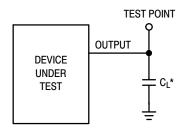
			Gu			
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	120 60 24 20	150 75 30 26	180 90 36 31	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	175 90 35 30	220 110 44 37	265 135 53 45	ns
t _{PZL} , t _{PZH}	Maximum Propagation Delay, Output Enable to Output Y (Figures 3 and 5)	2.0 3.0 4.5 6.0	190 95 38 32	240 120 48 21	285 150 57 48	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 2 and 4)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance	-	10	10	10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)		15	15	15	pF

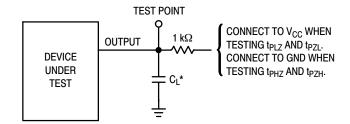
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Buffer)	EN IR RIV 60	pF

SWITCHING WAVEFORMS



TEST CIRCUITS

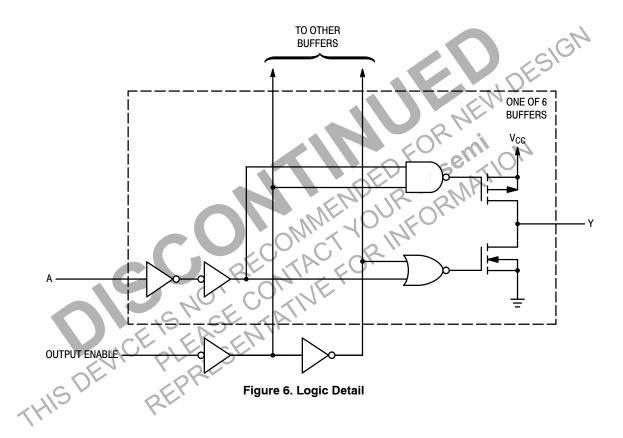




*Includes all probe and jig capacitance

Figure 4.

Figure 5.



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC367ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC367ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HC367ADTG	TSSOP-16 (Pb-Free)	96 Units / Tube
MC74HC367ADTR2G	TSSOP-16 (Pb-Free)	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

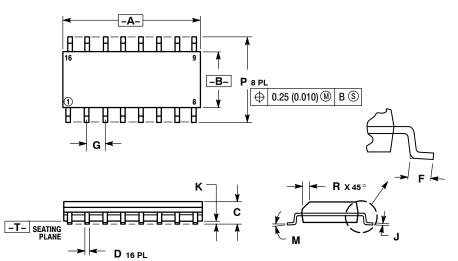
^{*}Includes all probe and jig capacitance





SOIC-16 CASE 751B-05 **ISSUE K**

DATE 29 DEC 2006



⊕ 0.25 (0.010) M T B S A S

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD ENGREPHING.

- PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
- DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR PROTRUSION.
 SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D
 DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
U	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:		
	COLLECTOR	PIN 1.	CATHODE	PIN 1.		PIN 1.	COLLECTOR, DYE #	1
2.	BASE	2.	ANODE	2.	BASE, #1	2.	COLLECTOR, #1	
3.	EMITTER	3.	NO CONNECTION	3.	EMITTER, #1	3.	COLLECTOR, #2	
4.	NO CONNECTION	4.	CATHODE	4.	COLLECTOR, #1	4.	COLLECTOR, #2	
5.	EMITTER	5.	CATHODE	5.	COLLECTOR, #2	5.	COLLECTOR, #3	
6.	BASE	6.	NO CONNECTION	6.	BASE, #2	6.	COLLECTOR, #3	
7.	COLLECTOR	7.	ANODE	7.	EMITTER, #2	7.	COLLECTOR, #4	
8.	COLLECTOR	8.	CATHODE	8.	COLLECTOR, #2	8.	COLLECTOR, #4	
9.	BASE	9.	CATHODE	9.	COLLECTOR, #3	9.	BASE, #4	
10.	EMITTER	10.	ANODE	10.	BASE, #3	10.	EMITTER, #4	
11.	NO CONNECTION	11.	NO CONNECTION	11.	EMITTER, #3	11.	BASE, #3	
12.	EMITTER	12.		12.	COLLECTOR, #3	12.	EMITTER, #3	
13.	BASE	13.		13.		13.	BASE, #2	RECOMMENDED
14.	COLLECTOR	14.	NO CONNECTION	14.		14.	EMITTER, #2	SOLDERING FOOTPRINT*
15.	EMITTER	15.	ANODE	15.	EMITTER, #4	15.	BASE, #1	
16.	COLLECTOR	16.	CATHODE	16.	COLLECTOR, #4	16.	EMITTER, #1	8X
								← 6.40 →
STYLE 5:		STYLE 6:		STYLE 7:				
PIN 1.	DRAIN, DYE #1		CATHODE		SOURCE N-CH			16X 1.12 <
2.	DRAIN, #1	2.	CATHODE	2.	COMMON DRAIN (OUTPU	T)		<u> </u>
3.	DRAIN, #2	3.	CATHODE	3.	COMMON DRAIN (OUTPU			1 16
4.	DRAIN, #2	4.	CATHODE	4.	GATE P-CH	,	<u>1</u>	
5.	DRAIN, #3	5.	CATHODE	5.	COMMON DRAIN (OUTPU	T)		
6.	DRAIN, #3	6.	CATHODE	6.	COMMON DRAIN (OUTPU	T)	16X 7	
7.	DRAIN, #4	7.	CATHODE	7.	COMMON DRAIN (OUTPU	T)	0.58	
8.	DRAIN, #4	8.	CATHODE	8.	SOURCE P-CH			
9.	GATE, #4	9.	ANODE	9.	SOURCE P-CH			
10.	SOURCE, #4	10.	ANODE	10.	COMMON DRAIN (OUTPU		_	
11.	GATE, #3	11.	ANODE	11.	COMMON DRAIN (OUTPU			
12.	SOURCE, #3	12.	ANODE	12.	COMMON DRAIN (OUTPU	T)		
13.	GATE, #2	13.	ANODE	13.	GATE N-CH			
14.	SOURCE, #2		ANODE	14.				
15.	GATE, #1	15.	ANODE	15.	COMMON DRAIN (OUTPU	Τ)		PITCH
16.	SOURCE, #1	16.	ANODE	16.	SOURCE N-CH			
								□□18 9 + □ +
								DIMENSIONS: MILLIMETERS

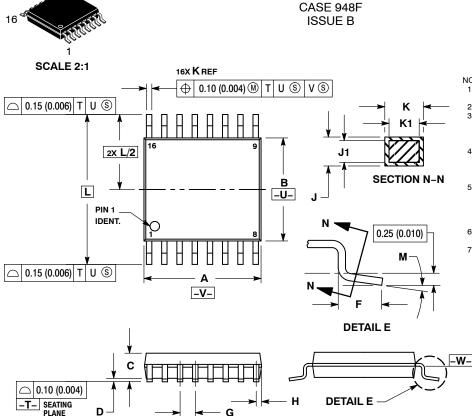
*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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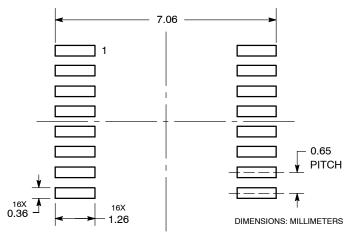
TSSOP-16 WB

NOTES

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT
- EXCEED 0.15 (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION SHALL
 NOT EXCEED 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABILE DAMBAR
 PROTRUSION SHALL BE 0.08 (0.003) TOTAL
 IN EXCESS OF THE K DIMENSION AT
 MAXIMUM MATERIAL CONDITION.
 TERMINIAL NILMBERS ADE SUCIUMI ECIP.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0 °	8°	0 °	8 °	

RECOMMENDED SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



= Specific Device Code XXXX Α = Assembly Location

= Wafer Lot L = Year W = Work Week G or • = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.

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